STARPOWER

SEMICONDUCTOR

FD100HFH120C1S

Molding Type Module

1200V/100A 2 in one-package

General Description

STARPOWER Diode Power Module provides low forward voltage as well as low reverse recovery loss. They are designed for the applications such as SMPS.

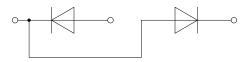
Features

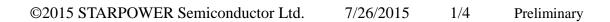
- Fast soft diode
- Low forward voltage drop
- Small temperature coefficient
- Low reverse recovery losses
- High ruggedness
- Low inductance
- Isolated copper baseplate using DBC technology

Typical Applications

- SMPS
- PFC
- Electric welders
- DC choppers

Equivalent Circuit Schematic







FRED

Symbol	Description	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	1200	V
I _F	Continuous Forward Current	100	А
I _{FRM}	Repetitive Peak Forward Current	200	А
P _D	Maximum Power Dissipation @ T _i =150°C	383	W
T _{jmax}	Maximum Junction Temperature	150	°C
T _{jop}	Operating Junction Temperature	-40 to +125	°C
T _{STG}	Storage Temperature Range	-40 to +125	°C
V _{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	2500	V

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Electrical Characteristics of Diode T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _F	Diode Forward	$I_{\rm F}=100{\rm A}, T_{\rm j}=25^{\rm o}{\rm C}$		1.82	2.27	V
	Voltage	$I_{\rm F}=100{\rm A}, T_{\rm j}=125^{\rm o}{\rm C}$		1.95		
Qr	Recovered			8.6		μC
	Charge	$ I_{F} = 100 A, V_{R} = 600 V \\ -di/dt = 1600 A/\mu s \\ T_{j} = 25^{\circ} C $		0.0		μ
I _{RM}	Peak Reverse			98		А
	Recovery Current					
E _{rec}	Reverse Recovery			4.24		mJ
	Energy			7.27		1115
Qr	Recovered			16.8		μC
	Charge	$I_F=100A, V_R=600V$ -di/dt=1600A/ μ s $T_i=125^{\circ}C$		10.0		μ
I _{RM}	Peak Reverse			118		А
	Recovery Current			110		Л
E _{rec}	Reverse Recovery	1j-125 C		7.27		mJ
	Energy					

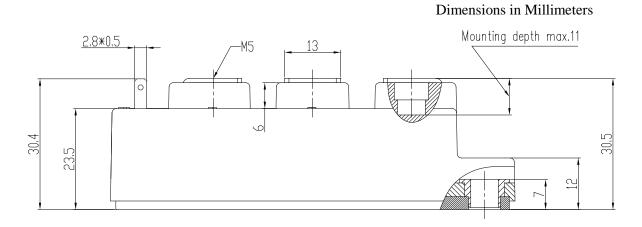
Thermal Characteristics

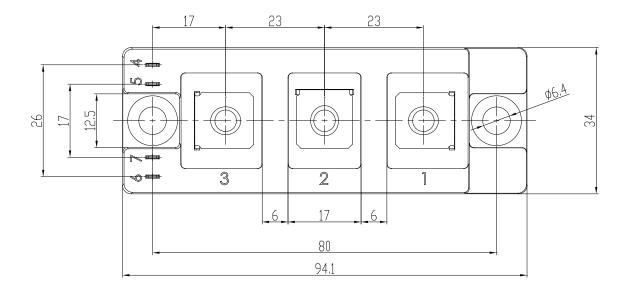
Symbol	Parameter	Min.	Тур.	Max.	Unit
L _{CE}	Stray Inductance			30	nH
R _{CC'+EE'}	Module Lead Resistance, Terminal to Chip		0.75		mΩ
R _{thJC}	Junction-to-Case (per Diode)			0.326	K/W
R _{thCH}	Case-to-Heatsink (per Module)		0.050		K/W
М	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		150		g

Equivalent Circuit Schematic



Package Dimensions





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